

=> d his ful

(FILE 'HOME' ENTERED AT 12:44:45 ON 11 FEB 2009)

FILE 'HCAPLUS' ENTERED AT 12:44:55 ON 11 FEB 2009

L1 1 SEA SPE=ON ABB=ON PLU=ON US20080241753/PN
 D L1 ALL
 SAV L1 LEE004/A
 SEL L1 RN

FILE 'REGISTRY' ENTERED AT 12:45:36 ON 11 FEB 2009

L2 9 SEA SPE=ON ABB=ON PLU=ON (138529-81-4/BI OR 144317-44-
 2/BI OR 17464-88-9/BI OR 188557-77-9/BI OR 3089-11-0/BI
 OR 357164-86-4/BI OR 4356-60-9/BI OR 475115-04-9/BI OR
 66003-78-9/BI)
 D SCA
 SAV L2 LEE004A/A

FILE 'LREGISTRY' ENTERED AT 12:49:12 ON 11 FEB 2009

L3 STR

FILE 'REGISTRY' ENTERED AT 12:52:48 ON 11 FEB 2009

L4 50 SEA SSS SAM L3

FILE 'LREGISTRY' ENTERED AT 14:01:00 ON 11 FEB 2009

L5 STR L3

FILE 'REGISTRY' ENTERED AT 14:04:57 ON 11 FEB 2009

L6 50 SEA SSS SAM L5

L7 50 SEA SSS SAM L5

L8 91465 SEA SSS FUL L5

 SAV L8 LEE004B/A

FILE 'LREGISTRY' ENTERED AT 14:09:24 ON 11 FEB 2009

L9 STR L5

FILE 'REGISTRY' ENTERED AT 14:12:36 ON 11 FEB 2009

L10 2 SEA SPE=ON ABB=ON PLU=ON L2 AND L8
 D SCA

FILE 'LREGISTRY' ENTERED AT 14:13:11 ON 11 FEB 2009

L11 STR L5

FILE 'REGISTRY' ENTERED AT 14:14:33 ON 11 FEB 2009

L12 1 SEA SUB=L8 SSS SAM (L9 AND L11)

FILE 'LREGISTRY' ENTERED AT 14:17:00 ON 11 FEB 2009

L13 STR L9

L14 STR L11

FILE 'REGISTRY' ENTERED AT 14:47:24 ON 11 FEB 2009

L15 3 SEA SUB=L8 SSS SAM (L13 AND L14)

L16 136 SEA SUB=L8 SSS FUL (L13 AND L14)

SAV L16 LEE004D/A

FILE 'HCAPLUS' ENTERED AT 14:49:17 ON 11 FEB 2009

L17 76 SEA SPE=ON ABB=ON PLU=ON L16

L18 125035 SEA SPE=ON ABB=ON PLU=ON RESIST# OR PHOTORESIST? OR
PHOTO#(W)RESIST?

L19 10 SEA SPE=ON ABB=ON PLU=ON L17 AND L18

L20 342967 SEA SPE=ON ABB=ON PLU=ON CROSSLINK? OR CROSS#(W)LINK?

L21 6 SEA SPE=ON ABB=ON PLU=ON L17 AND L20

L22 5 SEA SPE=ON ABB=ON PLU=ON L21 NOT L19

D L21 AN 6

D L19 10 AN

L23 1 SEA SPE=ON ABB=ON PLU=ON L17 AND PY<=2004 NOT P/DT

L24 75 SEA SPE=ON ABB=ON PLU=ON L17 AND (PRD<=20040319 OR
AY<=20040319 OR PD<=20040319) AND P/DT

FILE 'REGISTRY' ENTERED AT 15:10:50 ON 11 FEB 2009

L25 6 SEA SPE=ON ABB=ON PLU=ON L16 AND 2/NC

FILE 'HCAPLUS' ENTERED AT 15:16:46 ON 11 FEB 2009

L26 13 SEA SPE=ON ABB=ON PLU=ON L25

L27 6 SEA SPE=ON ABB=ON PLU=ON L26 NOT (L19 OR L22)

FILE 'REGISTRY' ENTERED AT 15:17:55 ON 11 FEB 2009

SAV L25 LEE404F/A

FILE HOME

FILE HCAPLUS

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FILE COVERS 1907 - 11 Feb 2009 VOL 150 ISS 7
FILE LAST UPDATED: 10 Feb 2009 (20090210/ED)

HCAplus now includes complete International Patent Classification (IPC) reclassification data for the third quarter of 2008.

CAS Information Use Policies apply and are available at:

<http://www.cas.org/legal/infopolicy.html>

This file contains CAS Registry Numbers for easy and accurate substance identification.

FILE REGISTRY

Property values tagged with IC are from the ZIC/VINITI data file provided by InfoChem.

STRUCTURE FILE UPDATES: 9 FEB 2009 HIGHEST RN 1103577-63-4
DICTIONARY FILE UPDATES: 9 FEB 2009 HIGHEST RN 1103577-63-4

New CAS Information Use Policies, enter HELP USAGETERMS for details.

TSCA INFORMATION NOW CURRENT THROUGH July 5, 2008.

Please note that search-term pricing does apply when conducting SmartSELECT searches.

REGISTRY includes numerically searchable data for experimental and predicted properties as well as tags indicating availability of experimental property data in the original document. For information on property searching in REGISTRY, refer to:

<http://www.cas.org/support/stngen/stndoc/properties.html>

FILE LREGISTRY

LREGISTRY IS A STATIC LEARNING FILE

NEW CAS INFORMATION USE POLICIES, ENTER HELP USAGETERMS FOR DETAILS.

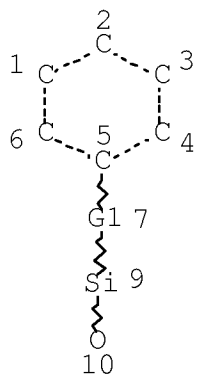
FILE STNGUIDE

FILE CONTAINS CURRENT INFORMATION.

LAST RELOADED: Feb 6, 2009 (20090206/UP).

=> d que stat l8

L5 STR



REP G1=(0-6) C

NODE ATTRIBUTES:

DEFAULT MLEVEL IS ATOM

DEFAULT ECLEVEL IS LIMITED

GRAPH ATTRIBUTES:

RSPEC 5

NUMBER OF NODES IS 9

STEREO ATTRIBUTES: NONE

L8 91465 SEA FILE=REGISTRY SSS FUL L5

100.0% PROCESSED 108989 ITERATIONS

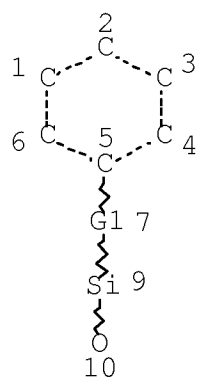
91465 ANSWERS

SEARCH TIME: 00.00.01

=> d que stat l16

L5 STR

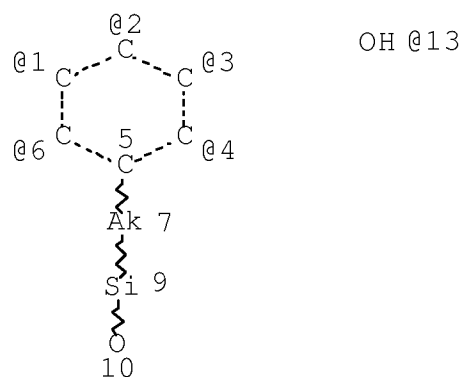
10/593,004



REP G1=(0-6) C
NODE ATTRIBUTES:
DEFAULT MLEVEL IS ATOM
DEFAULT ECLEVEL IS LIMITED

GRAPH ATTRIBUTES:
RSPEC 5
NUMBER OF NODES IS 9

STEREO ATTRIBUTES: NONE
L8 91465 SEA FILE=REGISTRY SSS FUL L5
L13 STR



VPA 13-1/2/3/4/6 U
NODE ATTRIBUTES:
DEFAULT MLEVEL IS ATOM
DEFAULT ECLEVEL IS LIMITED
ECOUNT IS M1-X5 C AT 7

10/593,004

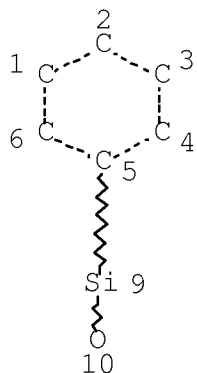
GRAPH ATTRIBUTES:

RSPEC 5

NUMBER OF NODES IS 10

STEREO ATTRIBUTES: NONE

L14 STR



NODE ATTRIBUTES:

DEFAULT MLEVEL IS ATOM

DEFAULT ECLEVEL IS LIMITED

GRAPH ATTRIBUTES:

RSPEC 5

NUMBER OF NODES IS 8

STEREO ATTRIBUTES: NONE

L16 136 SEA FILE=REGISTRY SUB=L8 SSS FUL (L13 AND L14)

100.0% PROCESSED 76875 ITERATIONS

136 ANSWERS

SEARCH TIME: 00.00.01

=> d l19 1-10 bib abs hitstr hitind

AN 2008:1243897 HCAPLUS Full-text
 DN 149:458344
 TI Nanoimprint resists containing substituted
 phenyl-containing silsesquioxanes and their patterns and patterning
 IN Takeuchi, Yoshiyuki; Ishikawa, Kiyoshi
 PA Tokyo Ohka Kogyo Co., Ltd., Japan
 SO Jpn. Kokai Tokkyo Koho, 15pp.
 CODEN: JKXXAF
 DT Patent
 LA Japanese
 FAN.CNT 2

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
	-----	----	-----	-----	
PI	JP 2008246876	A	20081016	JP 2007-91695	20070330
	WO 2008126523	A1	20081023	WO 2008-JP53988	20080305

W: AE, AG, AL, AM, AO, AT, AU, AZ, BA, BB, BG, BH, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DO, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IS, KE, KG, KM, KN, KP, KR, KZ, LA, LC, LK, LR, LS, LT, LU, LY, MA, MD, ME, MG, MK, MN, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RS, RU, SC, SD, SE, SG, SK, SL, SM, SV, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, ZA, ZM, ZW
 RW: AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HR, HU, IE, IS, IT, LT, LU, LV, MC, MT, NL, NO, PL, PT, RO, SE, SI, SK, TR, BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG, BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW, AM, AZ, BY, KG, KZ, MD, RU, TJ, TM

PRAI JP 2007-91695 A 20070330
 JP 2007-227089 A 20070831
 JP 2007-227090 A 20070831

AB Title resists contain silsesquioxanes containing Si(R2-p-C6H4OR1)O2/3 [R1 = H, C1-5 alkyl; R2 = single bond, C1-5 alkylene]. Because of the silsesquioxanes, the nanoimprint patterns, useful for lenses, show high transfer accuracy and good mold-release properties.

IT 475115-04-9 1002099-61-7
 RL: TEM (Technical or engineered material use); USES (Uses) (assumed monomers; substituted phenyl-containing silsesquioxane nanoimprint resists showing high transfer accuracy)

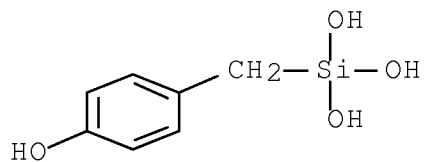
RN 475115-04-9 HCAPLUS
 CN Silanetriol, 1-[(4-hydroxyphenyl)methyl]-, polymer with 1-phenylsilanetriol (CA INDEX NAME)

10/593,004

CM 1

CRN 188557-76-8

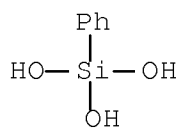
CMF C7 H10 O4 Si



CM 2

CRN 3047-74-3

CMF C6 H8 O3 Si



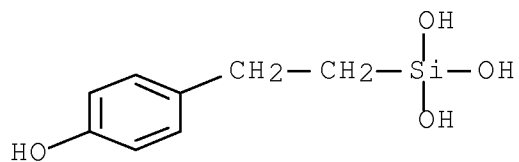
RN 1002099-61-7 HCAPLUS

CN Silanetriol, 1-[2-(4-hydroxyphenyl)ethyl]-, polymer with
1-phenylsilanetriol (CA INDEX NAME)

CM 1

CRN 546114-69-6

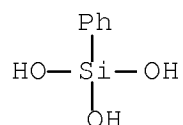
CMF C8 H12 O4 Si



CM 2

CRN 3047-74-3

CMF C6 H8 O3 Si



- CC 74-5 (Radiation Chemistry, Photochemistry, and Photographic and Other Reprographic Processes)
- ST hydroxybenzylsilanetriol phenylsilanetriol copolymer nanoimprint resist transfer accuracy
- IT Silsesquioxanes
 RL: TEM (Technical or engineered material use); USES (Uses)
 (Me, OCD T 9; substituted phenyl-containing silsesquioxane nanoimprint resists showing high transfer accuracy)
- IT Silsesquioxanes
 RL: TEM (Technical or engineered material use); USES (Uses)
 (hydrogen, OCD T 12; substituted phenyl-containing silsesquioxane nanoimprint resists showing high transfer accuracy)
- IT Lithography
 (nanoimprint; substituted phenyl-containing silsesquioxane nanoimprint resists showing high transfer accuracy)
- IT Silsesquioxanes
 RL: TEM (Technical or engineered material use); USES (Uses)
 (silicate-; substituted phenyl-containing silsesquioxane nanoimprint resists showing high transfer accuracy)
- IT Resists
 (substituted phenyl-containing silsesquioxane nanoimprint resists showing high transfer accuracy)
- IT 104133-11-1D, Methylsilanetriol homopolymer, polymers with silicates 157374-41-9, Phenylsilanetriol homopolymer 188557-77-9, p-Hydroxybenzylsilanetriol homopolymer 475115-04-9 1002099-61-7 1043891-50-4 1043891-51-5
 RL: TEM (Technical or engineered material use); USES (Uses)
 (assumed monomers; substituted phenyl-containing silsesquioxane

IT nanoimprint resists showing high transfer accuracy)
 681-84-5, OCD T 2 51350-55-1, Phenylsilanetriol homopolymer,
 ladder sru 112627-92-6, OCD Type 7 153315-80-1D,
 Methylsilanetriol homopolymer, ladder sru, polymers with silicates
 188629-68-7, p-Hydroxybenzylsilanetriol homopolymer, ladder sru
 RL: TEM (Technical or engineered material use); USES (Uses)
 (substituted phenyl-containing silsesquioxane nanoimprint
 resists showing high transfer accuracy)

L19 ANSWER 2 OF 10 HCAPLUS COPYRIGHT 2009 ACS on STN

AN 2007:1420012 HCAPLUS Full-text

DN 148:67464

TI Method of forming resist pattern by nanoimprint
 lithography

IN Sato, Kazufumi; Yamada, Tomotaka

PA Tokyo Ohka Kogyo Co., Ltd., Japan

SO PCT Int. Appl., 31pp.

CODEN: PIXXD2

DT Patent

LA Japanese

FAN.CNT 1

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
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PI	WO 2007142088	A1	20071213	WO 2007-JP60956	20070530
W:	AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BH, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DO, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IS, KE, KG, KM, KN, KP, KR, KZ, LA, LC, LK, LR, LS, LT, LU, LY, MA, MD, MG, MK, MN, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RS, RU, SC, SD, SE, SG, SK, SL, SM, SV, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, ZA, ZM, ZW				
RW:	AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IS, IT, LT, LU, LV, MC, MT, NL, PL, PT, RO, SE, SI, SK, TR, BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG, BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW, AM, AZ, BY, KG, KZ, MD, RU, TJ, TM				
	JP 2007329276	A	20071220	JP 2006-158894	20060607

PRAI JP 2006-158894 A 20060607

AB Provided is a method of forming a resist pattern of high aspect ratio
 excelling in etching resistance using nanoimprint lithog. The method
 of forming a resist pattern by nanoimprint lithog. comprises the

steps of disposing organic layer on support; providing resist layer on the organic layer using chemical amplification type neg. resist composition containing silsesquioxane resin; pressing light transmission allowing mold with partial light shielding portion against the resist layer and thereafter carrying out exposure from the upside of the mold; and detaching the mold.

IT 475115-04-9

RL: TEM (Technical or engineered material use); USES (Uses)
(use of molds in forming resist pattern by nanoimprint lithog.)

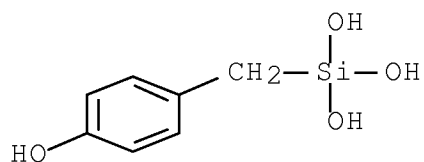
RN 475115-04-9 HCAPLUS

CN Silanetriol, 1-[(4-hydroxyphenyl)methyl]-, polymer with 1-phenylsilanetriol (CA INDEX NAME)

CM 1

CRN 188557-76-8

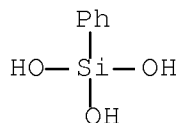
CMF C7 H10 O4 Si



CM 2

CRN 3047-74-3

CMF C6 H8 O3 Si



CC 76-3 (Electric Phenomena)

ST resist pattern nanoimprint lithog silsesquioxane resin;
mold exposure

IT Photolithography
 (nanoprint; use of molds in forming resist pattern by
 nanoimprint lithog.)

IT Molds (forms)
 Photoresists
 Semiconductor device fabrication
 (use of molds in forming resist pattern by nanoimprint
 lithog.)

IT Silsesquioxanes
 RL: TEM (Technical or engineered material use); USES (Uses)
 (use of molds in forming resist pattern by nanoimprint
 lithog.)

IT 193345-23-2 227199-92-0 475115-04-9 959860-10-7
 RL: TEM (Technical or engineered material use); USES (Uses)
 (use of molds in forming resist pattern by nanoimprint
 lithog.)

RE.CNT 16 THERE ARE 16 CITED REFERENCES AVAILABLE FOR THIS RECORD
 ALL CITATIONS AVAILABLE IN THE RE FORMAT

L19 ANSWER 3 OF 10 HCAPLUS COPYRIGHT 2009 ACS on STN
 AN 2006:272812 HCAPLUS Full-text
 DN 144:321539
 TI Composition for forming antireflective film and electric wiring
 forming method using same
 IN Tanaka, Takeshi; Sakamoto, Yoshinori; Takahama, Masaru
 PA Tokyo Ohka Kogyo Co., Ltd., Japan
 SO PCT Int. Appl., 34 pp.
 CODEN: PIXXD2
 DT Patent
 LA Japanese
 FAN.CNT 1

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
WO 2006030641	A1	20060323	WO 2005-JP15907	20050831

W: AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA,
 CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI,
 GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, KE, KG, KM, KP,
 KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW,
 MX, MZ, NA, NG, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC,
 SD, SE, SG, SK, SL, SM, SY, TJ, TM, TN, TR, TT, TZ, UA, UG,
 US, UZ, VC, VN, YU, ZA, ZM, ZW

RW: AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU,
 IE, IS, IT, LT, LU, LV, MC, NL, PL, PT, RO, SE, SI, SK, TR,
 BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD,

TG, BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM,
ZW, AM, AZ, BY, KG, KZ, MD, RU, TJ, TM

JP 2006084799 A 20060330 JP 2004-269705

200409
16

CN 101010635 A 20070801 CN 2005-80029662

200508
31

TW 279647 B 20070421 TW 2005-94130960

200509
08

KR 2007040827 A 20070417 KR 2007-705137

200703
02

US 20080318165 A1 20081225 US 2007-575299

200703
14

PRAI JP 2004-269705 A 20040916

WO 2005-JP15907 W 20050831

AB Disclosed is an antireflective film-forming material which enables to obtain a large etching rate difference between a resist pattern and an antireflective film. Specifically disclosed is a composition for forming antireflective films which contains a siloxane polymer (A) containing a light absorptive compound group.

IT 475115-04-9

RL: TEM (Technical or engineered material use); USES (Uses)
(composition for forming antireflective film and wiring forming

method

using same)

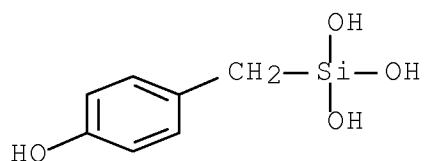
RN 475115-04-9 HCAPLUS

CN Silanetriol, 1-[(4-hydroxyphenyl)methyl]-, polymer with
1-phenylsilanetriol (CA INDEX NAME)

CM 1

CRN 188557-76-8

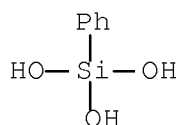
CMF C7 H10 O4 Si



CM 2

CRN 3047-74-3

CMF C6 H8 O3 Si



CC 74-5 (Radiation Chemistry, Photochemistry, and Photographic and Other Reprographic Processes)
 Section cross-reference(s): 76

IT Antireflective films
 Photolithography
 Photoresists
 Printed circuit boards
 (composition for forming antireflective film and wiring forming method using same)

IT 159873-52-6, Tetramethoxysilane/methyltrimethoxysilane copolymer
 475115-04-9
 RL: TEM (Technical or engineered material use); USES (Uses)
 (composition for forming antireflective film and wiring forming method using same)

RE.CNT 14 THERE ARE 14 CITED REFERENCES AVAILABLE FOR THIS RECORD
 ALL CITATIONS AVAILABLE IN THE RE FORMAT

L19 ANSWER 4 OF 10 HCAPLUS COPYRIGHT 2009 ACS on STN

AN 2005:1049149 HCAPLUS Full-text

DN 143:356596

TI Negative-working resist composition containing polysilsesquioxane

IN Ando, Tomoyuki

PA Tokyo Ohka Kogyo Co., Ltd., Japan

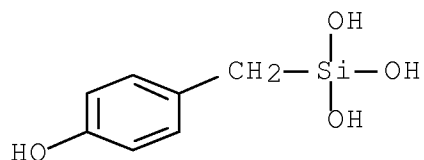
SO Jpn. Kokai Tokkyo Koho, 25 pp.
 CODEN: JKXXAF

DT Patent

LA Japanese

FAN.CNT 1

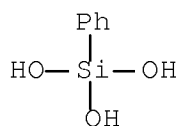
	PATENT NO. ----- -----	KIND ----	DATE -----	APPLICATION NO. -----	DATE
PI	JP 2005266474	A	20050929	JP 2004-80481	20040319
	WO 2005091073	A1	20050929	WO 2005-JP4326	20050311
	W: AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NA, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SM, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM, ZW RW: BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW, AM, AZ, BY, KG, KZ, MD, RU, TJ, TM, AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IS, IT, LT, LU, MC, NL, PL, PT, RO, SE, SI, SK, TR, BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG				
	EP 1726992	A1	20061129	EP 2005-720597	20050311
	R: DE				
	US 20080241753	A1	20081002	US 2006-593004	20060914
PRAI	JP 2004-80481	A	20040319		
	WO 2005-JP4326	W	20050311		
AB	Disclosed is a neg.-working resist composition comprising (a) a silsesquioxane resin having units of [Si(-R1-C6H4-OH)O3/2] (R1 = C1-5 alkylene) and [SiPhO3/2], (b) an acid-generating compound, and (c) a crosslinking agent.				
IT	475115-04-9P				
	RL: IMF (Industrial manufacture); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses) (neg.-working electron-beam resist composition containing polysilsesquioxane)				
RN	475115-04-9 HCAPLUS				
CN	Silanetriol, 1-[(4-hydroxyphenyl)methyl]-, polymer with 1-phenylsilanetriol (CA INDEX NAME)				
CM	1				
CRN	188557-76-8				
CMF	C7 H10 O4 Si				



CM 2

CRN 3047-74-3

CMF C6 H8 O3 Si



IC ICM G03F007-038
ICS C08G077-16; G03F007-075; H01L021-027

CC 74-5 (Radiation Chemistry, Photochemistry, and Photographic and
Other Reprographic Processes)
Section cross-reference(s): 38

ST neg working electron beam resist compn polysilsesquioxane

IT Electron beam resists
Resists
(neg.-working electron-beam resist composition containing
polysilsesquioxane)

IT Silsesquioxanes
RL: TEM (Technical or engineered material use); USES (Uses)
(neg.-working electron-beam resist composition containing
polysilsesquioxane)

IT 66003-78-9, Triphenylsulfonium trifluoromethane sulfonate
138529-81-4, Bis(cyclohexylsulfonyl)diazomethane 144317-44-2,
Triphenylsulfonium nonafluorobutane sulfonate 357164-86-4
RL: TEM (Technical or engineered material use); USES (Uses)
(acid-generating agent; neg.-working electron-beam resist
composition containing polysilsesquioxane)

IT 3089-11-0 4356-60-9 17464-88-9

RL: TEM (Technical or engineered material use); USES (Uses)
 (crosslinker; neg.-working electron-beam resist composition
 containing polysilsesquioxane)

IT 188557-77-9P 475115-04-9P

RL: IMF (Industrial manufacture); TEM (Technical or engineered
 material use); PREP (Preparation); USES (Uses)
 (neg.-working electron-beam resist composition containing
 polysilsesquioxane)

L19 ANSWER 5 OF 10 HCAPLUS COPYRIGHT 2009 ACS on STN

AN 2005:612362 HCAPLUS Full-text

DN 143:134159

TI Organopolysiloxane curable composition

IN Morita, Yoshitsugu; Isshiki, Minoru; Ueki, Hiroshi; Enami, Hiroji

PA Dow Corning Toray Silicone Co., Ltd., Japan

SO PCT Int. Appl., 31 pp.

CODEN: PIXXD2

DT Patent

LA Japanese

FAN.CNT 1

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
	-----	----	-----	-----	
PI	WO 2005063843	A1	20050714	WO 2004-JP19489	200412 20
W:	AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NA, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM, ZW				
RW:	BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW, AM, AZ, BY, KG, KZ, MD, RU, TJ, TM, AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IS, IT, LT, LU, MC, NL, PL, PT, RO, SE, SI, SK, TR, BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG				
EP 1702938	A1	20060920	EP 2004-807844	200412 20	
EP 1702938	B1	20080924			
R:	AT, BE, CH, DE, DK, ES, FR, GB, GR, IT, LI, LU, NL, SE, MC, PT, IE, SI, LT, FI, RO, CY, TR, BG, CZ, EE, HU, PL, SK, IS				
CN 1906226	A	20070131	CN 2004-80040671	200412 20	

AT	409201	T	20081015	AT	2004-807844	
						200412
						20
KR	2007004594	A	20070109	KR	2006-715037	
						200607
						25
US	20070282058	A1	20071206	US	2007-584655	
						200707
						06

PRAI JP 2003-433628 A 20031226
 WO 2004-JP19489 W 20041220

AB A silicone composition comprises (A) an organopolysiloxane having a branched-chain structure and containing at least two monovalent hydrocarbon groups with phenolic hydroxyl group, as shown in the general formula $[R1SiO_{1/2}]_a[R2SiO]_b[R3SiO_{3/2}]_c$ (wherein, R1, R2 and R3 are C1-C12 organic groups; $a+b+c=1$; $0 \leq a \leq 0.8$; $0 \leq b \leq 0.8$; $0.2 \leq c \leq 1.0$); (B) a linear organopolysiloxane containing at least two monovalent hydrocarbon groups with epoxy group but without aromatic ring, as shown in the general formula $R7SiO(R8SiO)_mSiR73$ (wherein, R7 and R8 are C1-C12 organic groups; m is an integer from 1 to 1000); (C) a curing accelerator; and (D) filler. Thus, a silicone composition prepared from 25.0 parts of $[Z(CH_3)_2SiO_{1/2}]_0.6[C_6H_5SiO_{3/2}]_0.4$ (wherein, Z is 3-(m-hydroxyphenyl)propyl group), 14.0 parts of X- $(CH_3)_2SiO(CH_3)_2Si-X$ (wherein, X is 3-glycidoxypropyl), 1.0 part of catalyst HX 3088, and 60.0 parts of silica filler Admafine, shows viscosity of 15 Pa·s, thermal expansion coefficient of 110 ppm/°C, complex viscoelastic modulus of 80 MPa, curing time of 45 min, and good adhesiveness to solder resist, nickel, copper, aluminum and glass.

IT 858341-40-9 858341-41-0
 RL: POF (Polymer in formulation); PRP (Properties); TEM (Technical or engineered material use); USES (Uses)
 (organopolysiloxane curable composition)

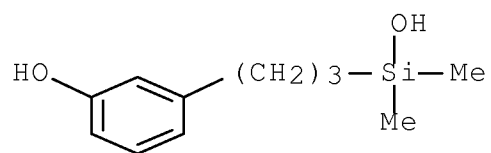
RN 858341-40-9 HCAPLUS

CN Silanetriol, phenyl-, polymer with
 [3-(3-hydroxyphenyl)propyl]dimethylsilanol and
 1,1,3,3-tetramethyl-1,3-bis[3-(oxiranylmethoxy)propyl]disiloxane
 (9CI) (CA INDEX NAME)

CM 1

CRN 858341-39-6
 CMF C11 H18 O2 Si

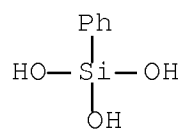
10/593,004



CM 2

CRN 3047-74-3

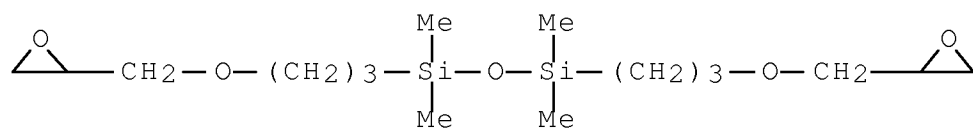
CMF C6 H8 O3 Si



CM 3

CRN 126-80-7

CMF C16 H34 O5 Si2



RN 858341-41-0 HCAPLUS

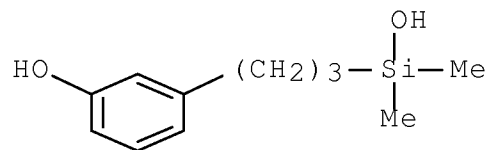
CN Silanetriol, phenyl-, polymer with
[3-(3-hydroxyphenyl)propyl]dimethylsilanol,
1,1,3,3-tetramethyl-1,3-bis[3-(oxiranylmethoxy)propyl]disiloxane and
trimethoxy[3-(oxiranylmethoxy)propyl]silane (9CI) (CA INDEX NAME)

CM 1

10/593,004

CRN 858341-39-6

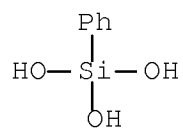
CMF C11 H18 O2 Si



CM 2

CRN 3047-74-3

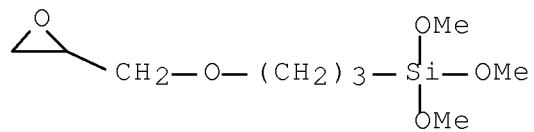
CMF C6 H8 O3 Si



CM 3

CRN 2530-83-8

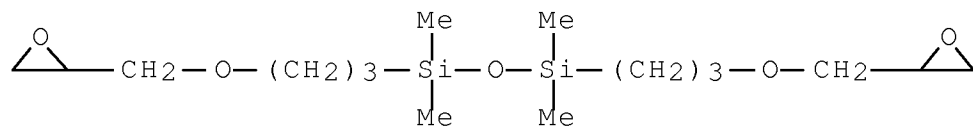
CMF C9 H20 O5 Si



CM 4

CRN 126-80-7

CMF C16 H34 O5 Si2



IC ICM C08G059-62
 CC 37-6 (Plastics Manufacture and Processing)
 IT 858341-40-9 858341-41-0 858341-42-1
 RL: POF (Polymer in formulation); PRP (Properties); TEM (Technical or engineered material use); USES (Uses)
 (organopolysiloxane curable composition)
 RE.CNT 6 THERE ARE 6 CITED REFERENCES AVAILABLE FOR THIS RECORD
 ALL CITATIONS AVAILABLE IN THE RE FORMAT

L19 ANSWER 6 OF 10 HCAPLUS COPYRIGHT 2009 ACS on STN
 AN 2004:534428 HCAPLUS Full-text
 DN 141:79326
 TI Chemical amplification type silicone base positive photoresist composition
 IN Hirayama, Taku; Yamada, Tomotaka; Kawana, Daisuke; Tamura, Kouki; Sato, Kazufumi
 PA Tokyo Ohka Kogyo Co., Ltd., Japan
 SO PCT Int. Appl., 34 pp.
 CODEN: PIXXD2
 DT Patent
 LA Japanese
 FAN.CNT 1

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
WO 2004055598	A1	20040701	WO 2003-JP15344	20031201

W: AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM, ZW
 RW: BW, GH, GM, KE, LS, MW, MZ, SD, SL, SZ, TZ, UG, ZM, ZW, AM,

AZ, BY, KG, KZ, MD, RU, TJ, TM, AT, BE, BG, CH, CY, CZ, DE,
 DK, EE, ES, FI, FR, GB, GR, HU, IE, IT, LU, MC, NL, PT, RO,
 SE, SI, SK, TR, BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML,
 MR, NE, SN, TD, TG

AU 2003302990	A1	20040709	AU 2003-302990	20031201
DE 10393820	T5	20051027	DE 2003-10393820	20031201
TW 282040	B	20070601	TW 2003-92133901	20031202
US 20060003252	A1	20060105	US 2005-537290	20050622

PRAI JP 2002-350563 A 20021202
 JP 2003-46611 A 20030224
 JP 2003-190618 A 20030702
 WO 2003-JP15344 W 20031201

AB A chemical amplification type silicone base pos. resist composition that can be produced from easily procurable compds. as raw materials through simple means and can provide a bilayer resist material from which fine pattern of high resolution, high aspect ratio, desirable sectional morphol. and low line edge roughness can be formed. In particular, a chemical amplification type pos. resist composition comprising alkali soluble resin (A) and photoacid generator (B) wherein a ladder type silicone copolymer comprising (hydroxyphenylalkyl)silsesquioxane units (a1), (alkoxyphenylalkyl)silsesquioxane units (a2) and alkyl- or phenylsilsesquioxane units (a3) is used as the alkali soluble resin (A). The copolymer wherein in the component (A), the units (a3) are phenylsilsesquioxane units is a novel compound

IT 711008-00-3
 RL: TEM (Technical or engineered material use); USES (Uses)
 (chemical amplification type silicone base pos. photoresist composition)

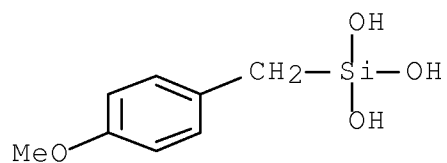
RN 711008-00-3 HCAPLUS

CN Silanetriol, 1-[(4-hydroxyphenyl)methyl]-, polymer with 1-[(4-methoxyphenyl)methyl]silanetriol and 1-phenylsilanetriol (CA INDEX NAME)

CM 1

CRN 546114-67-4

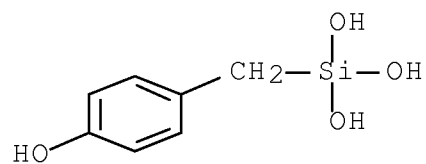
CMF C8 H12 O4 Si



CM 2

CRN 188557-76-8

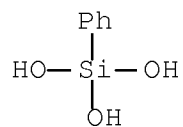
CMF C7 H10 O4 Si



CM 3

CRN 3047-74-3

CMF C6 H8 O3 Si



IC ICM G03F007-11

ICS C08G077-14; H01L021-027

CC 74-5 (Radiation Chemistry, Photochemistry, and Photographic and Other Reprographic Processes)

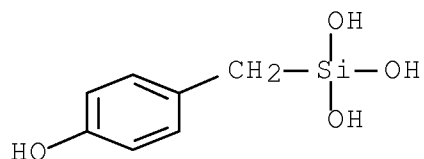
Section cross-reference(s): 38

ST chem amplification silicone photoresist compn

silsesquioxane
 IT Photoresists
 (chemical amplification type silicone base pos. photoresist
 composition)
 IT 711008-00-3
 RL: TEM (Technical or engineered material use); USES (Uses)
 (chemical amplification type silicone base pos. photoresist
 composition)
 IT 102-71-6, Triethanolamine, uses 102-82-9, Tributylamine
 1571-33-1, Phenylphosphonic acid
 RL: TEM (Technical or engineered material use); USES (Uses)
 (quencher; chemical amplification type silicone base pos.
 photoresist composition)
 RE.CNT 18 THERE ARE 18 CITED REFERENCES AVAILABLE FOR THIS RECORD
 ALL CITATIONS AVAILABLE IN THE RE FORMAT

L19 ANSWER 7 OF 10 HCAPLUS COPYRIGHT 2009 ACS on STN
 AN 2002:869229 HCAPLUS Full-text
 DN 137:377441
 TI Photoimageable resist composition containing specific
 polysilsesquioxane for bilayer resist system
 IN Gronbeck, Dana A.; Barclay, George G.; Linehan, Leo L.; Xiong, Kao;
 Kanagasabapathy, Subareddy
 PA Shipley Company, LLC, USA
 SO PCT Int. Appl., 65 pp.
 CODEN: PIXXD2
 DT Patent
 LA English
 FAN.CNT 1

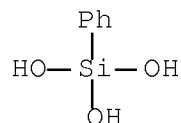
PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
-----	----	-----	-----	
PI WO 2002091083	A1	20021114	WO 2002-US14732	200205 08
W: AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NO, NZ, OM, PH, PL, PT, RO, RU, SD, SE, SG, SI, SK, SL, TJ, TM, TN, TR, TT, TZ, UA, UG, UZ, VN, YU, ZA, ZM, ZW				
RW: GH, GM, KE, LS, MW, MZ, SD, SL, SZ, TZ, UG, ZM, ZW, AT, BE, CH, CY, DE, DK, ES, FI, FR, GB, GR, IE, IT, LU, MC, NL, PT, SE, TR, BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG				
TW 594416	B	20040621	TW 2002-91109417	200205



CM 2

CRN 3047-74-3

CMF C6 H8 O3 Si



IC ICM G03F007-029

ICS G03F007-032; G03F007-004; G03C001-725

CC 74-5 (Radiation Chemistry, Photochemistry, and Photographic and Other Reprographic Processes)

IT Light-sensitive materials

Photoresists

(photoimaging composition containing specific polysilsesquioxane)

IT 475115-04-9

RL: TEM (Technical or engineered material use); USES (Uses)

(photoimaging composition containing specific polysilsesquioxane)

RE.CNT 10 THERE ARE 10 CITED REFERENCES AVAILABLE FOR THIS RECORD

ALL CITATIONS AVAILABLE IN THE RE FORMAT

L19 ANSWER 8 OF 10 HCAPLUS COPYRIGHT 2009 ACS on STN

AN 1994:689666 HCAPLUS Full-text

DN 121:289666

OREF 121:52719a,52722a

TI Photoresist composition

IN Kobayashi, Yoshihito

PA Tokyo Shibaura Electric Co, Japan

SO Jpn. Kokai Tokkyo Koho, 41 pp.

CODEN: JKXXAF

DT Patent

LA Japanese

FAN.CNT 1

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
-----	----	-----	-----	

PI JP 06075377	A	19940318	JP 1992-226130	199208

PRAI JP 1992-226130 19920825

AB The title composition comprises an alkali-soluble polymer, a compound having a substituent decomposing by an acid, and a photo acid generator, R2SO3CR1R3C.tplbond.CC.tplbond.CCR4R6O3SR5 [R1-6 = aromatic hydrocarbyl, heterocyclyl, aliphatic hydrocarbyl, characteristic group, H]. The composition showed high sensitivity to both deep UV and ionization radiation and was alkali-developable.

IT 159103-14-7 159103-16-9 159103-24-9
 RL: DEV (Device component use); TEM (Technical or engineered material use); USES (Uses)
 (deep UV sensitive alkali-developable photoresist composition)

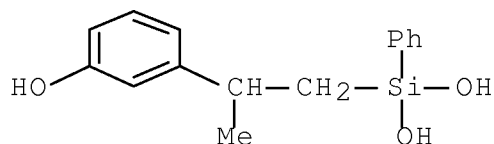
RN 159103-14-7 HCAPLUS

CN Silanediol, diphenyl-, polymer with
 [2-(3-hydroxyphenyl)propyl]phenylsilanediol (9CI) (CA INDEX NAME)

CM 1

CRN 159103-13-6

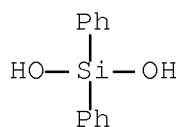
CMF C15 H18 O3 Si



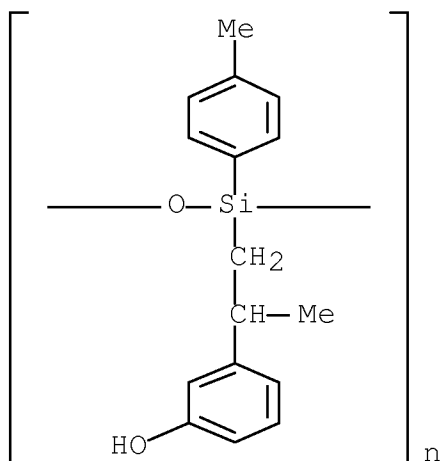
CM 2

CRN 947-42-2

CMF C12 H12 O2 Si



RN 159103-16-9 HCAPLUS

CN Poly[oxy[[2-(3-hydroxyphenyl)propyl](4-methylphenyl)silylene]] (9CI)
(CA INDEX NAME)

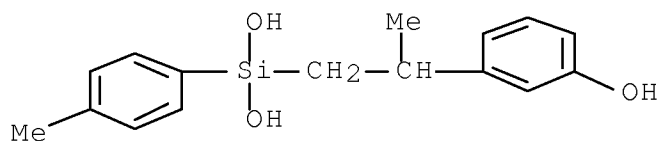
RN 159103-24-9 HCAPLUS

CN Silanediol, [2-(3-hydroxyphenyl)propyl](4-methylphenyl)-,
homopolymer (9CI) (CA INDEX NAME)

CM 1

CRN 159103-23-8

CMF C16 H20 O3 Si



IC ICM G03F007-039

ICS C08K005-42; C08L101-00; G03F007-004; H01L021-312

CC 74-5 (Radiation Chemistry, Photochemistry, and Photographic and
Other Reprographic Processes)
Section cross-reference(s): 76

ST photoresist compn photo acid generator

IT Polycarbosilanes
Siloxanes and Silicones, uses
RL: DEV (Device component use); TEM (Technical or engineered material use); USES (Uses)
(deep UV sensitive alkali-developable photoresist composition)

IT Phenolic resins, uses
RL: DEV (Device component use); TEM (Technical or engineered material use); USES (Uses)
(novolak, cresol-based, m, p-cresol novolak resin; deep UV sensitive alkali-developable photoresist composition)

IT Resists
(photo-, deep UV sensitive photoresist composition)

IT 24979-70-2, Poly(p-vinylphenol) 159103-11-4 159103-12-5
159103-14-7 159103-15-8 159103-16-9
159103-20-5 159103-22-7 159103-24-9
RL: DEV (Device component use); TEM (Technical or engineered material use); USES (Uses)
(deep UV sensitive alkali-developable photoresist composition)

IT 117458-06-7 127669-88-9 138888-97-8 142952-62-3 143897-55-6
143897-56-7 143897-58-9 143897-61-4 159103-06-7 159103-07-8
159103-17-0 159103-18-1
RL: CAT (Catalyst use); TEM (Technical or engineered material use); USES (Uses)
(development inhibitor in deep UV sensitive alkali-developable photoresist composition)

IT 32527-15-4 73130-96-8 120551-36-2 149873-03-0 149873-13-2
159103-08-9 159103-09-0 159103-10-3
RL: CAT (Catalyst use); TEM (Technical or engineered material use); USES (Uses)
(photo acid generator in deep UV sensitive alkali-developable photoresist composition)

L19 ANSWER 9 OF 10 HCAPLUS COPYRIGHT 2009 ACS on STN

AN 1989:622152 HCAPLUS Full-text

DN 111:222152

OREF 111:36733a,36736a

TI Photosensitive composition containing azide compound for high-precision pattern

IN Horiguchi, Rumiko; Hayase, Shuzi; Onishi, Yasunobu; Ushirogouchi, Toru

PA Toshiba Corp., Japan

SO Ger. Offen., 36 pp.

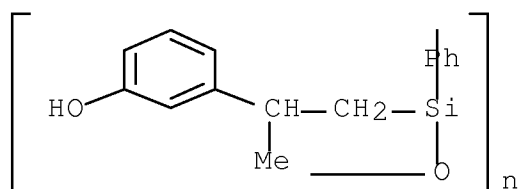
CODEN: GWXXBX

DT Patent

LA German

FAN.CNT 1

	PATENT NO. -----	KIND ----	DATE -----	APPLICATION NO. -----	DATE
PI	DE 3841571	A1	19890629	DE 1988-3841571	19881209
	JP 01154047	A	19890616	JP 1987-312657	19871210
	JP 01154048	A	19890616	JP 1987-312658	19871210
	JP 01161336	A	19890626	JP 1987-320414	19871218
	JP 01241544	A	19890926	JP 1988-68387	19880323
	DE 3844739	C2	19950907	DE 1988-3844739	19881209
PRAI	JP 1987-312657	A	19871210		
	JP 1987-312658	A	19871210		
	JP 1987-320414	A	19871218		
	JP 1988-68387	A	19880323		
	DE 1988-3841571	A3	19881209		
AB	A photosensitive composition is described containing an alkali-soluble resin, optionally a Si-containing resin, and a compound sensitive to 248 nm deep UV radiation and having the formula R1COC(N2)COR2 [I; R1, R2 = C1-20 alkyl or alkoxy, aryl, aryloxy, anilino]. Optionally the photosensitive compds. are Si-containing compds. of the formula R2R3R4 SiC(N2)R1 [R1-R4 = H, C1-10 alkyl, aryl, silyl]. The preferred compds. of the formula I are aromatic compds. in which ≥ 1 benzene ring is substituted with ≥ 1 O2CC(N2)COMe group.				
IT	123710-88-3 RL: USES (Uses) (binder, for deep UV photoresist)				
RN	123710-88-3 HCAPLUS				
CN	Poly[oxy[[2-(3-hydroxyphenyl)propyl]phenylsilylene]] (9CI) (CA INDEX NAME)				



IC ICM G03F007-10
ICS G03F007-08; C08L025-18; C08L061-04

CC 74-5 (Radiation Chemistry, Photochemistry, and Photographic and Other Reprographic Processes)

ST photosensitive compn photoresist pattern; azide silane
photosensitive compd; binder photosensitive compd; phenolic resin
photosensitive compd

IT Phenolic resins, uses and miscellaneous
RL: USES (Uses)
(binders, for deep UV photoresist)

IT Binding materials
Azides
RL: USES (Uses)
(for deep UV photoresist)

IT Resists
(photo-, deep UV, azides for)

IT 25086-15-1, Methacrylic acid-methyl methacrylate copolymer
27029-76-1 59269-51-1, Polyvinylphenol 72317-19-2 85229-30-7,
Acrylonitrile-isopropenylphenol copolymer 100346-90-5,
m-Cresol-p-cresol-formaldehyde-2,5-xilenol copolymer 102868-49-5
104426-15-5 104426-16-6 111634-04-9 112504-03-7,
m-Cresol-p-cresol-formaldehyde-3,5-xilenol copolymer
123710-88-3 123737-03-1 123737-04-2 123737-05-3
123737-07-5 123737-09-7
RL: USES (Uses)
(binder, for deep UV photoresist)

IT 2009-96-3 2085-31-6 22760-66-3 24379-49-5 28383-65-5
41657-71-0 75742-13-1 86997-48-0 123131-57-7 123766-64-3
123766-65-4 123766-66-5 123766-67-6 123766-68-7 123766-69-8
123766-70-1 123766-71-2 123766-72-3 123766-73-4 123766-74-5
123766-75-6 123766-76-7 123766-77-8 123766-78-9 123766-79-0
123783-62-0 123783-63-1
RL: USES (Uses)
(photosensitive compound, for deep UV photoresist)

RE.CNT 3 THERE ARE 3 CITED REFERENCES AVAILABLE FOR THIS RECORD
ALL CITATIONS AVAILABLE IN THE RE FORMAT

L19 ANSWER 10 OF 10 HCAPLUS COPYRIGHT 2009 ACS on STN

AN 1989:125491 HCAPLUS Full-text

DN 110:125491

OREF 110:20537a,20540a

TI Photosensitive coating composition containing silicon-containing polymer

IN Horiguchi, Rumiko; Hayase, Shuzi; Onishi, Yasunobu

PA Toshiba Corp., Japan

SO Ger. Offen., 44 pp.

CODEN: GWXXBX

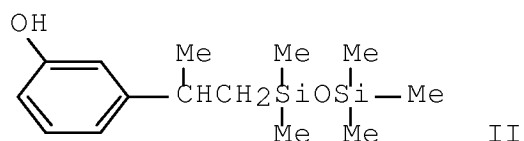
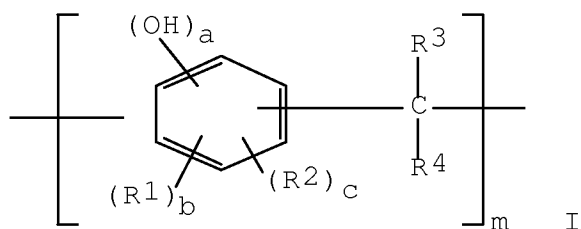
DT Patent

LA German

FAN.CNT 1

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
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PI	DE 3810247	A1	19881006	DE 1988-3810247	198803 25
	DE 3810247	C2	19930128		
	JP 63237052	A	19881003	JP 1987-72113	198703 26
	JP 01088447	A	19890403	JP 1987-245497	198709 29
	JP 01107254	A	19890425	JP 1987-263965	198710 21
	US 5063134	A	19911105	US 1990-455783	199001 02
PRAI	JP 1987-72113	A	19870326		
	JP 1987-245497	A	19870929		
	JP 1987-263965	A	19871021		
	US 1988-173546	B1	19880325		

GI



AB The title composition contains a photosensitive material and a polymer having recurring units of the formula I [R1-R4 = H, alkyl, alkoxy, alkyl; ≥ 1 of R1-R4 is a Si-containing C1-10 alkyl group; m = pos. integer; a, b = 1-3; c = 0-2; $a + b + c \leq 4$]. The material has improved resistance to O plasma and can be used in photolithog. applications. Thus, a mixture of II-m-cresol-p-cresol-HCHO copolymer and 2,3,4-trihydroxybenzophenone bis(1,2-naphthoquinone-2-diazido-5-sulfonate) was used to form a photoresist layer.

IT 119608-22-9 119608-29-6

RL: USES (Uses)

(photoresist containing)

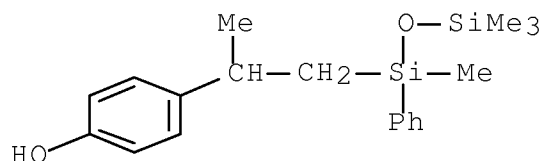
RN 119608-22-9 HCAPLUS

CN Formaldehyde, polymer with 3-methylphenol and 4-[1-methyl-2-(1,3,3,3-tetramethyl-1-phenyldisiloxanyl)ethyl]phenol (9CI) (CA INDEX NAME)

CM 1

CRN 119608-21-8

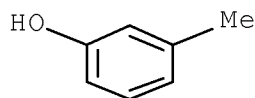
CMF C19 H28 O2 Si2



CM 2

CRN 108-39-4

CMF C7 H8 O

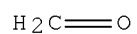


10/593,004

CM 3

CRN 50-00-0

CMF C H2 O



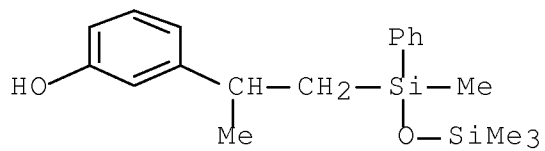
RN 119608-29-6 HCAPLUS

CN Formaldehyde, polymer with 3-methylphenol and
3-[1-methyl-2-(1,3,3,3-tetramethyl-1-phenyldisiloxanyl)ethyl]phenol
(9CI) (CA INDEX NAME)

CM 1

CRN 119608-28-5

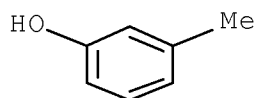
CMF C19 H28 O2 Si2



CM 2

CRN 108-39-4

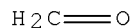
CMF C7 H8 O



CM 3

CRN 50-00-0

CMF C H2 O



IC ICM G03F007-00
 ICS G03F007-08; G03C001-72
 ICA C08L061-04; C09D003-54; C09D003-81; H01L021-312
 CC 74-6 (Radiation Chemistry, Photochemistry, and Photographic and
 Other Reprographic Processes)
 ST photolithog silicon contg polymer photoresist
 IT Resists
 (photo-, silicon-containing polymer for)
 IT Phenolic resins, uses and miscellaneous
 RL: USES (Uses)
 (silicon-containing, photoresists containing)
 IT 119588-16-8 119588-17-9 119588-19-1 119588-20-4 119588-21-5
 119588-23-7 119588-25-9 119588-27-1 119588-29-3 119588-30-6
 119588-31-7 119588-32-8 119588-34-0 119588-35-1 119608-20-7
 119608-22-9 119608-23-0 119608-25-2 119608-27-4
 119608-29-6 119608-31-0 119608-32-1 119608-33-2
 119608-34-3 119608-35-4 119608-37-6 119608-38-7 119608-40-1
 RL: USES (Uses)
 (photoresist containing)
 IT 75578-77-7 75578-79-9 75742-13-1 109478-62-8 119564-70-4
 RL: USES (Uses)
 (photoresist containing Si-containing polymer and)
 RE.CNT 1 THERE ARE 1 CITED REFERENCES AVAILABLE FOR THIS RECORD
 ALL CITATIONS AVAILABLE IN THE RE FORMAT

=> d 122 1-5 bib abs hitstr hitind

AN 2008:447443 HCAPLUS Full-text
 DN 148:427784
 TI Curable silicone composition and cured body thereof
 IN Morita, Yoshitsugu; Kato, Tomoko; Ueki, Hiroshi
 PA Dow Corning Toray Co., Ltd., Japan
 SO PCT Int. Appl., 30pp.
 CODEN: PIXXD2
 DT Patent
 LA English
 FAN.CNT 1

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
WO 2008041459	A1	20080410	WO 2007-JP67770	20070905
W: AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BH, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DO, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IS, KE, KG, KM, KN, KP, KR, KZ, LA, LC, LK, LR, LS, LT, LU, LY, MA, MD, ME, MG, MK, MN, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RS, RU, SC, SD, SE, SG, SK, SL, SM, SV, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, ZA, ZM, ZW RW: AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IS, IT, LT, LU, LV, MC, MT, NL, PL, PT, RO, SE, SI, SK, TR, BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG, BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW, AM, AZ, BY, KG, KZ, MD, RU, TJ, TM				
JP 2008081676	A	20080410	JP 2006-265955	20060928

PRAI JP 2006-265955 A 20060928
 AB A curable silicone composition comprises: (A) a diorganopolysiloxane represented by the following general formula: $\text{XR}_2(\text{R}_1\text{SiO})_m\text{R}_1\text{SiR}_2\text{X}$ [where R1 designates a monovalent hydrocarbon group that has six or fewer carbon atoms and is free of aliphatic unsatd. bonds; R2 designates an alkylene group; and X is an organopolysiloxane residue represented by the following average unit formula: $(\text{YR}_1\text{SiO}_{1/2})_a(\text{SiO}_{4/2})_b$ (where R1 is the same as defined above; Y is a single bond, a hydrogen atom, a group represented by aforementioned R1, an epoxy-containing alkyl group, an alkoxy-silylalkyl group, or an alkyl group with seven or more carbon atoms; however, in one mol., at least one Y is a single bond, and at least one Y is an alkyl group with seven or more carbon atoms; "a" is a pos. number; "b" is a pos. number; and "a/b" is a number in the range of 0.2 to 4.0), the aforementioned group represented by R1 or an alkenyl group; however,

at least one X is the aforementioned organopolysiloxane residue; and "m" is an integer equal to or greater than 1] and (B) a curing agent for epoxy resin. The composition has good handleability and, when cured, forms a cured silicone body having low modulus of elasticity.

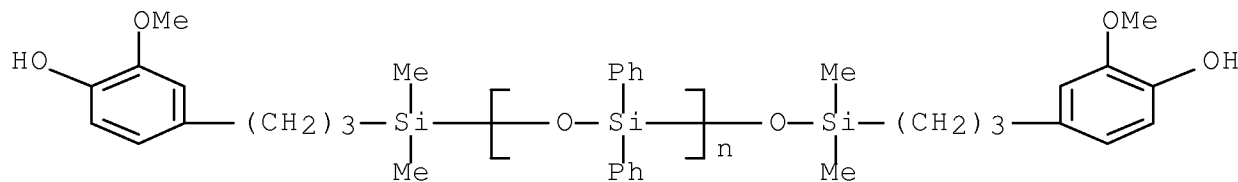
IT 537708-34-2

RL: TEM (Technical or engineered material use); USES (Uses)
(curable silicone composition and cured body thereof)

RN 537708-34-2 HCAPLUS

CN Poly[oxy(diphenylsilylene)],

α -[[3-(4-hydroxy-3-methoxyphenyl)propyl]dimethylsilyl]- ω -
[[[3-(4-hydroxy-3-methoxyphenyl)propyl]dimethylsilyl]oxy]- (CA
INDEX NAME)



CC 37-6 (Plastics Manufacture and Processing)

IT Crosslinking agents

(curable silicone composition and cured body thereof)

IT 106-92-3, Allylglycidylether 112-88-9, 1-Octadecene 872-05-9,
1-Decene 2551-83-9, Allyltrimethoxysilane 25068-38-6,
Bisphenol-A epoxy resin 58421-55-9 158167-48-7
537708-34-2

RL: TEM (Technical or engineered material use); USES (Uses)
(curable silicone composition and cured body thereof)

RE.CNT 3 THERE ARE 3 CITED REFERENCES AVAILABLE FOR THIS RECORD
ALL CITATIONS AVAILABLE IN THE RE FORMAT

L22 ANSWER 2 OF 5 HCAPLUS COPYRIGHT 2009 ACS on STN

AN 2008:353339 HCAPLUS Full-text

DN 148:356589

TI Thermally conductive, curable silicone composition and electronic component

IN Morita, Yoshitsugu; Isshiki, Minoru; Kato, Tomoko

PA Dow Corning Toray Co., Ltd., Japan

SO PCT Int. Appl., 34pp.

CODEN: PIXXD2

DT Patent

LA English

FAN.CNT 1

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
WO 2008032575	A1	20080320	WO 2007-JP66829	20070823
W: AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BH, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DO, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IS, KE, KG, KM, KN, KP, KR, KZ, LA, LC, LK, LR, LS, LT, LU, LY, MA, MD, ME, MG, MK, MN, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RS, RU, SC, SD, SE, SG, SK, SL, SM, SV, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, ZA, ZM, ZW RW: AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IS, IT, LT, LU, LV, MC, MT, NL, PL, PT, RO, SE, SI, SK, TR, BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG, BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW, AM, AZ, BY, KG, KZ, MD, RU, TJ, TM JP 2008063542 A 20080321 JP 2006-246080 20060911				

PRAI JP 2006-246080 A 20060911

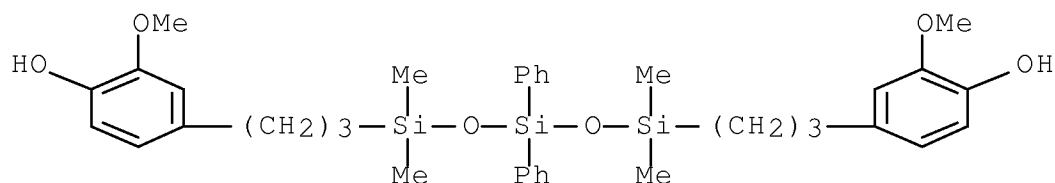
AB A curable silicone composition comprising at least the following components: (A) an epoxy-containing organopolysiloxane; (B) a curing agent for an epoxy resin; (C) a thermally conductive metal powder; and (D) a thermally conductive nonmetal powder; exhibits low viscosity, excellent handleability and curability and, when cured, forms a cured body of flexibility, low sp. gr., and excellent thermal conductivity. An electronic component sealed or adhesively bonded with use of a cured body obtained by curing the aforementioned composition provides high reliability.

IT 910040-29-8

RL: TEM (Technical or engineered material use); USES (Uses)
 (thermally conductive, curable silicone composition and electronic component)

RN 910040-29-8 HCAPLUS

CN Phenol, 4,4'-[(1,1,5,5-tetramethyl-3,3-diphenyl-1,5-trisiloxanediyl)di-3,1-propanediyl]bis[2-methoxy- (CA INDEX NAME)



CC 37-6 (Plastics Manufacture and Processing)
 Section cross-reference(s): 76

IT Adhesives
 Crosslinking agents
 Sealing compositions
 Semiconductor devices
 (thermally conductive, curable silicone composition and electronic component)

IT 9016-00-6D, Polydimethylsiloxane, hydroxyphenyl-terminated
 910040-29-8
 RL: TEM (Technical or engineered material use); USES (Uses)
 (thermally conductive, curable silicone composition and electronic component)

RE.CNT 5 THERE ARE 5 CITED REFERENCES AVAILABLE FOR THIS RECORD
 ALL CITATIONS AVAILABLE IN THE RE FORMAT

L22 ANSWER 3 OF 5 HCAPLUS COPYRIGHT 2009 ACS on STN
 AN 2007:993056 HCAPLUS Full-text
 DN 147:345203
 TI Semiconductor devices with good scratch resistance and low warpage
 and their manufacture
 IN Morita, Koji; Isshiki, Minoru; Ueki, Hiroshi; Kato, Tomoko
 PA Dow Corning Toray Co., Ltd., Japan
 SO Jpn. Kokai Tokkyo Koho, 28pp.
 CODEN: JKXXAF
 DT Patent
 LA Japanese

FAN.CNT 1

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
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JP 2007224146	A	20070906	JP 2006-46872	20060223
WO 2007099823	A1	20070907	WO 2007-JP53131	20070214

W: AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IS, KE, KG, KM, KN, KP, KR, KZ, LA, LC, LK, LR, LS, LT, LU, LV, LY, MA, MD, MG, MK, MN, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RS, RU, SC, SD, SE, SG, SK, SL, SM, SV, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, ZA, ZM, ZW
 RW: AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IS, IT, LT, LU, LV, MC, NL, PL, PT, RO, SE, SI, SK, TR, BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG, BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW, AM, AZ, BY, KG, KZ, MD, RU, TJ, TM

EP 1986832 A1 20081105 EP 2007-714631

200702

14

R: AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IS, IT, LI, LT, LU, LV, MC, NL, PL, PT, RO, SE, SI, SK, TR

KR 2008108089 A 20081211 KR 2008-720670

200808

22

PRAI JP 2006-46872 A 20060223

WO 2007-JP53131 W 20070214

AB The manufacturing method includes setting semiconductor devices in molds, feeding curable silicone compns. between the molds and the devices, and compression-molding so as to package, wherein the compns. include epoxy-containing silicones and curing agents. Thus, a composition with viscosity at 25° 140 Pa-s and complex modulus 730 MPa comprising XCH₂CH₂(Me₂SiO)₃Me₂SiCH₂CH₂X [X is siloxane residue of (GMe₂SiO_{1/2})₉(-Me₂SiO_{1/2})₁(SiO_{4/2})₆, G is 3-glycidoxypropyl] 31.0, 2,2'-[(1,1,5,5-tetramethyl-3,3-diphenyl-1,5-trisiloxanediyl)di-3,1-propanediyl]bisphenol 14.0, capsulated amine curing accelerator (HX 3721) 10.0, spherical amorphous silica (Admafine) 60.0, and 3-glycidoxypropyltrimethoxysilane 1 part was applied on a semiconductor chip-mounted circuit board, compression-molded, and heated to give a packaged device showing thickness difference between the central and circumferential parts <5% and warpage 2 mm.

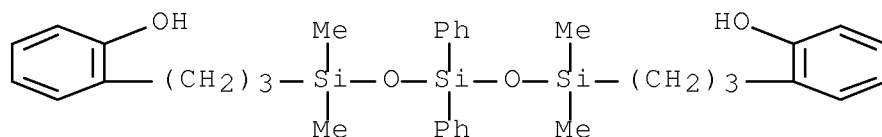
IT 910040-28-7 910040-29-8

RL: RCT (Reactant); RACT (Reactant or reagent)

(crosslinker; manufacture of semiconductor devices with good scratch resistance and low warpage)

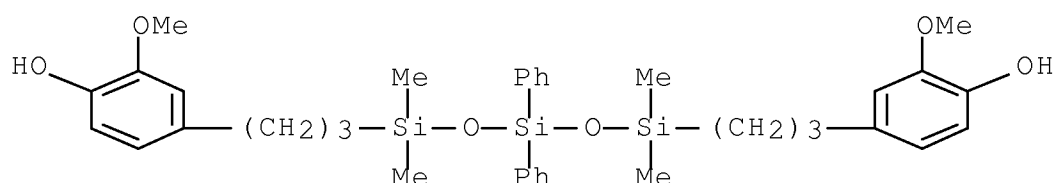
RN 910040-28-7 HCAPLUS

CN Phenol, 2,2'-[(1,1,5,5-tetramethyl-3,3-diphenyl-1,5-trisiloxanediyl)di-3,1-propanediyl]bis- (CA INDEX NAME)



RN 910040-29-8 HCAPLUS

CN Phenol, 4,4'-[(1,1,5,5-tetramethyl-3,3-diphenyl-1,5-trisiloxanediy)di-3,1-propanediyl]bis[2-methoxy- (CA INDEX NAME)



CC 38-3 (Plastics Fabrication and Uses)
Section cross-reference(s): 76

IT Polysiloxanes, uses

RL: POF (Polymer in formulation); TEM (Technical or engineered material use); USES (Uses)

(di-Me, epoxy-containing, crosslinked; manufacture of semiconductor devices with good scratch resistance and low warpage)

IT Silsesquioxanes

RL: POF (Polymer in formulation); TEM (Technical or engineered material use); USES (Uses)

(epoxy-containing, crosslinked; manufacture of semiconductor devices with good scratch resistance and low warpage)

IT Coupling agents

Crosslinking catalysts

Electronic packaging materials

Fillers

Semiconductor device fabrication

(manufacture of semiconductor devices with good scratch resistance

and

low warpage)

IT 25068-38-6, Epikote 828 51350-55-1D, Phenylsilanetriol homopolymer, ladder sru, dimethyl(3-glycidoxy)propylsilyl-terminated 157374-41-9D, Phenylsilanetriol homopolymer,

dimethyl(glycidoxy)propylsilyl-terminated

RL: POF (Polymer in formulation); TEM (Technical or engineered material use); USES (Uses)

(crosslinked; manufacture of semiconductor devices with good scratch resistance and low warpage)

IT 9016-00-6D, Poly[oxy(dimethylsilylene)],
dimethyl[3-(o-hydroxyphenyl)propyl]silyl-terminated 31900-57-9D,
Dimethylsilanediol homopolymer,
dimethyl[3-(o-hydroxyphenyl)propyl]silyl-terminated
910040-28-7 910040-29-8

RL: RCT (Reactant); RACT (Reactant or reagent)

(crosslinker; manufacture of semiconductor devices with good scratch resistance and low warpage)

L22 ANSWER 4 OF 5 HCAPLUS COPYRIGHT 2009 ACS on STN

AN 2006:978171 HCAPLUS Full-text

DN 145:357617

TI Curable silicone composition and electronic device produced therefrom

IN Morita, Yoshitsugu; Isshiki, Minoru; Ueki, Hiroshi; Kato, Tomoko

PA Dow Corning Toray Co., Ltd., Japan

SO PCT Int. Appl., 38pp.

CODEN: PIXXD2

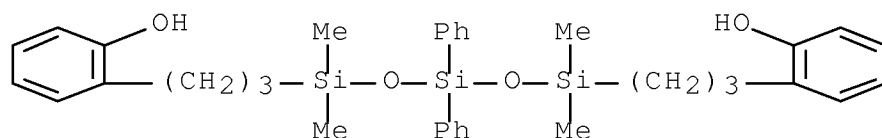
DT Patent

LA English

FAN.CNT 1

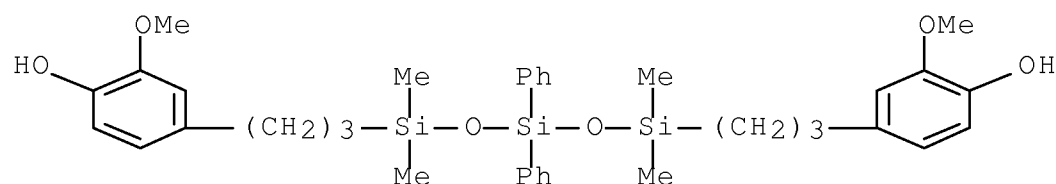
PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
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PI WO 2006098493	A1	20060921	WO 2006-JP305639	20060315
W: AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, KE, KG, KM, KN, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, LY, MA, MD, MG, MK, MN, MW, MX, MZ, NA, NG, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SM, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM, ZW RW: AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IS, IT, LT, LU, LV, MC, NL, PL, PT, RO, SE, SI, SK, TR, BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG, BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW, AM, AZ, BY, KG, KZ, MD, RU, TJ, TM				
JP 2006257115	A	20060928	JP 2005-72395	20050315

EP 1858983	A1	20071128	EP 2006-729606	200603 15
EP 1858983	B1	20080917		
R: AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IS, IT, LI, LT, LU, LV, MC, NL, PL, PT, RO, SE, SI, SK, TR				
AT 408649	T	20081015	AT 2006-729606	200603 15
KR 2007117597	A	20071212	KR 2007-721226	200709 14
CN 101142280	A	20080312	CN 2006-80008265	200709 14
PRAI JP 2005-72395	A	20050315		
WO 2006-JP305639	W	20060315		
AB	<p>A curable silicone composition comprising: (A) a diorganosiloxane represented by the following general formula: $AR_2(R_1SiO)_nR_1SiR_2A$ {wherein R_1 represents the same or different optionally substituted univalent hydrocarbon groups that do not have unsatd. aliphatic bonds; R_2 represents bivalent organic groups; A designates siloxane residual radicals represented by the following average unit formula: $(XR_1SiO_{1/2})_a(SiO_{4/2})_b$ (wherein R_1 designates the previously mentioned group; X designates a single bond, hydrogen atom, the previously mentioned group that is designated by R_1, an epoxy-containing alkyl group, or an alkoxy-silylalkyl group; at least one X in one mol. is a single bond; at least two X's are epoxy-containing alkyl groups; a is a pos. number, b is a pos. number; and a/b is a pos. number within the range of 0.2 to 4), and n is an integer which is equal to or greater than 1}; and (B) a curing agent for an epoxy resin, is characterized by excellent handle ability and curability and that is suitable for curing into a cured body that has excellent flexibility and adhesive characteristics; to provide a highly reliable electronic device. Typical (B) is a phenolic compound, and, the composition contains an amine-type accelerator.</p>			
IT	<p>910040-28-7 910040-29-8</p> <p>RL: MOA (Modifier or additive use); TEM (Technical or engineered material use); USES (Uses)</p> <p>(crosslinking agent; thermosetting epoxy group-containing silicone compns. for flexible adhesives for manufacture of electronic devices)</p>			
RN	910040-28-7 HCAPLUS			
CN	Phenol, 2,2'-[(1,1,5,5-tetramethyl-3,3-diphenyl-1,5-trisiloxanediyl)di-3,1-propanediyl]bis- (CA INDEX NAME)			



RN 910040-29-8 HCAPLUS

CN Phenol, 4,4'-[(1,1,5,5-tetramethyl-3,3-diphenyl-1,5-trisiloxanediyl)di-3,1-propanediyl]bis[2-methoxy- (CA INDEX NAME)



CC 37-6 (Plastics Manufacture and Processing)

Section cross-reference(s): 76

IT Phenols, uses

RL: MOA (Modifier or additive use); TEM (Technical or engineered material use); USES (Uses)

(crosslinking agent; thermosetting epoxy group-containing silicone compns. for flexible adhesives for manufacture of electronic devices)

IT Amines, uses

RL: CAT (Catalyst use); USES (Uses)

(crosslinking catalyst; thermosetting epoxy group-containing silicone compns. for flexible adhesives for manufacture of electronic devices)

IT 2530-83-8, 3-Glycidyloxypropyltrimethoxysilane 25068-38-6, Epikote 828

RL: MOA (Modifier or additive use); TEM (Technical or engineered material use); USES (Uses)

(addnl. crosslinkable component; thermosetting epoxy group-containing silicone compns. for flexible adhesives for manufacture

of electronic devices)
IT 910107-81-2, Silicic acid, dimethyl-3-(glycidyloxy)propylsilyl ester
RL: TEM (Technical or engineered material use); USES (Uses)
(addnl. crosslinkable component; thermosetting epoxy
group-containing silicone compns. for flexible adhesives for
manufacture
of electronic devices)
IT 25550-51-0, HN-5500 27924-97-6, MEH 8000 31900-57-9D,
Dimethylsilanediol homopolymer, hydroxyphenyl-terminated
158167-48-7 163617-00-3 191875-74-8 910040-28-7
910040-29-8
RL: MOA (Modifier or additive use); TEM (Technical or engineered
material use); USES (Uses)
(crosslinking agent; thermosetting epoxy group-containing
silicone compns. for flexible adhesives for manufacture of
electronic
devices)
IT 288-32-4D, Imidazole, derivs. 134633-76-4, HX 3721 146702-27-4,
HX 3941HP 149779-74-8, HX 3088 910113-00-7, HXA 4921HP
910113-01-8, Amicure PN 3
RL: CAT (Catalyst use); USES (Uses)
(crosslinking catalyst; thermosetting epoxy
group-containing silicone compns. for flexible adhesives for
manufacture
of electronic devices)
RE.CNT 5 THERE ARE 5 CITED REFERENCES AVAILABLE FOR THIS RECORD
ALL CITATIONS AVAILABLE IN THE RE FORMAT

L22 ANSWER 5 OF 5 HCAPLUS COPYRIGHT 2009 ACS on STN
AN 1997:276826 HCAPLUS Full-text
DN 126:344382
OREF 126:66967a,66970a
TI Hybrid Organic/Inorganic Copolymers with Strongly Hydrogen-Bond
Acidic Properties for Acoustic Wave and Optical Sensors
AU Grate, Jay W.; Kaganove, Steven N.; Patrash, Samuel J.; Craig,
Richard; Bliss, Mary
CS Environmental Molecular Sciences Laboratory Engineering and Analytic
Sciences Department, Pacific Northwest National Laboratory,
Richland, WA, 99352, USA
SO Chemistry of Materials (1997), 9(5), 1201-1207
CODEN: CMATEX; ISSN: 0897-4756
PB American Chemical Society
DT Journal
LA English
AB Hybrid organic/inorg. polymers have been prepared incorporating
fluoroalkyl-substituted bisphenol groups linked using oligosiloxane
spacers. These hydrogen-bond acidic materials have glass-to-rubber

transition temps. below room temperature and are excellent sorbents for basic vapors. The phys. properties such as viscosity and refractive index can be tuned by varying the length of the oligosiloxane spacers and the mol. weight. In addition, the materials are easily cross-linked to yield solid elastomers. The potential use of these materials for chemical sensing has been demonstrated by applying them to surface acoustic wave devices as thin films and detecting the hydrogen-bond basic vapor di-Me methylphosphonate with high sensitivity. It has also been demonstrated that one of these materials with suitable viscosity and refractive index can be used to clad silica optical fibers; the cladding was applied to freshly drawn fiber using a fiber drawing tower. These fibers have potential as evanescent wave optical fiber sensors.

IT 189892-82-8F

RL: PRP (Properties); SPN (Synthetic preparation); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)

(rubber; preparation of hybrid organic/inorg. siloxane elastomers

with

strongly hydrogen-bond acidic properties for acoustic wave and optical sensors)

RN 189892-82-8 HCAPLUS

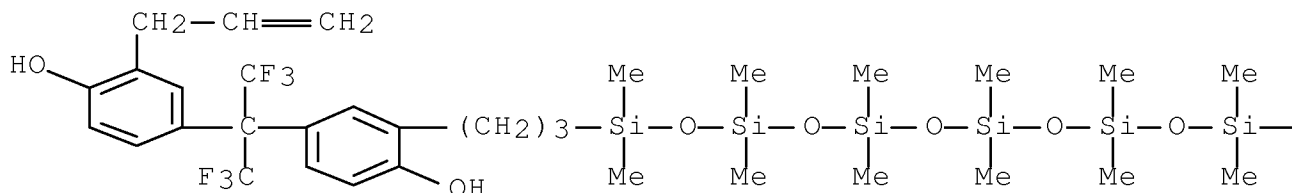
CN Phenol, 4,4'-[(1,1,3,3,5,5,7,7,9,9,11,11-dodecamethyl-1,11-hexasiloxanediyl)bis[3,1-propanediyl(4-hydroxy-3,1-phenylene)[2,2,2-trifluoro-1-(trifluoromethyl)ethylidene]]]bis[2-(2-propenyl)-, polymer with 3-[(dimethylsilyl)oxy]-1,1,5,5-tetramethyl-3-phenyltrisiloxane (9CI) (CA INDEX NAME)

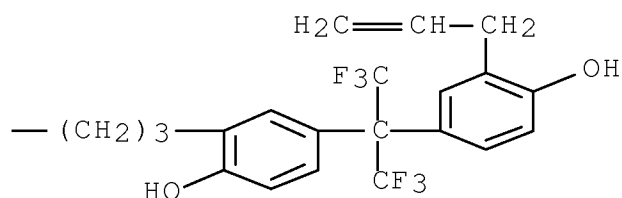
CM 1

CRN 189892-81-7

CMF C54 H74 F12 O9 Si6

PAGE 1-A

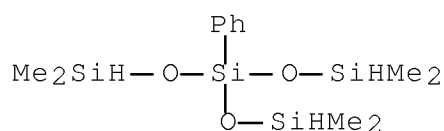




CM 2

CRN 18027-45-7

CMF C12 H26 O3 Si4



CC 39-15 (Synthetic Elastomers and Natural Rubber)

Section cross-reference(s): 38, 73

ST elastomeric fluoro siloxane crosslinkable polymer prepn;
cladding bisallyl hexafluorobisphenol terminated crosslinked
siloxane; surface acoustic wave sensor hybrid siloxane; sorbent
crosslinked bisallylhexafluoro bisphenol siloxane copolymer

IT Crosslinking

Glass transition temperature

Surface acoustic wave sensors

(preparation of hybrid organic/inorg. siloxane elastomers with
strongly
hydrogen-bond acidic properties for acoustic wave and optical
sensors)

IT 170346-91-5, PC 085

RL: CAT (Catalyst use); USES (Uses)

(crosslinking catalyst; preparation of hybrid organic/inorg.
siloxane elastomers with strongly hydrogen-bond acidic properties
for acoustic wave and optical sensors)

IT 189892-82-8P

RL: PRP (Properties); SPN (Synthetic preparation); TEM (Technical or
engineered material use); PREP (Preparation); USES (Uses)

(rubber; preparation of hybrid organic/inorg. siloxane elastomers
with strongly hydrogen-bond acidic properties for acoustic wave and
optical sensors)

RE.CNT 38 THERE ARE 38 CITED REFERENCES AVAILABLE FOR THIS RECORD
ALL CITATIONS AVAILABLE IN THE RE FORMAT

=> d 127 1-6 bib abs hitstr hitind

YOU HAVE REQUESTED DATA FROM FILE 'HCAPLUS' - CONTINUE? (Y)/N:y

L27 ANSWER 1 OF 6 HCAPLUS COPYRIGHT 2009 ACS on STN

AN 2008:1280393 HCAPLUS Full-text

DN 149:472683

TI Film forming composition for nanoimprinting, process for production
of structures, and structures

IN Takeuchi, Yoshiyuki; Ishikawa, Kiyoshi

PA Tokyo Ohka Kogyo Co., Ltd., Japan

SO PCT Int. Appl., 37pp.

CODEN: PIXXD2

DT Patent

LA Japanese

FAN.CNT 2

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
-----	----	-----	-----	
PI WO 2008126523	A1	20081023	WO 2008-JP53988	20080305
W:	AE, AG, AL, AM, AO, AT, AU, AZ, BA, BB, BG, BH, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DO, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IS, KE, KG, KM, KN, KP, KR, KZ, LA, LC, LK, LR, LS, LT, LU, LY, MA, MD, ME, MG, MK, MN, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RS, RU, SC, SD, SE, SG, SK, SL, SM, SV, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, ZA, ZM, ZW			
RW:	AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HR, HU, IE, IS, IT, LT, LU, LV, MC, MT, NL, NO, PL, PT, RO, SE, SI, SK, TR, BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG, BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW, AM, AZ, BY, KG, KZ, MD, RU, TJ, TM			
JP 2008246876	A	20081016	JP 2007-91695	200703

PRAI JP 2007-91695 A 20070330
 JP 2007-227089 A 20070831
 JP 2007-227090 A 20070831

AB The film-forming composition for nanoimprinting which permits high-precision pattern transfer from a mold and is good in the close adhesion to a substrate and the peelability of a mold, comprises silsesquioxane resin having structure unit $-\text{[Si(R}_2\text{-p-C}_6\text{H}_4\text{OR}_1\text{)}\text{O}_3\text{/}_2\text{]}-$ (R₁ = H, C₁-5 alkyl; R₂ = mono-bond, C₁-5 alkylene). A process for the production of structures with improved thermal stability comprises coating a base with the film-forming composition to form a film; molding; and peeling the resin layer from the mold. Further, after the peeling of a mold in the production of a structure, it is preferable to irradiate the resin layer with UV light under a reduced pressure.

IT 475115-04-9P 1002099-61-7P

RL: IMF (Industrial manufacture); PEP (Physical, engineering or chemical process); TEM (Technical or engineered material use); PREP (Preparation); PROC (Process); USES (Uses)
 (silsesquioxane resin film forming composition for nanoimprinting)

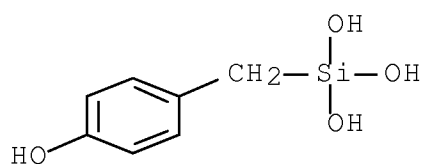
RN 475115-04-9 HCAPLUS

CN Silanetriol, 1-[(4-hydroxyphenyl)methyl]-, polymer with 1-phenylsilanetriol (CA INDEX NAME)

CM 1

CRN 188557-76-8

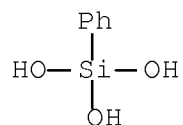
CMF C7 H10 O4 Si



CM 2

CRN 3047-74-3

CMF C6 H8 O3 Si



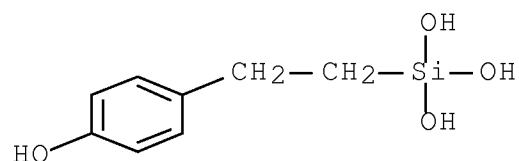
RN 1002099-61-7 HCAPLUS

CN Silanetriol, 1-[2-(4-hydroxyphenyl)ethyl]-, polymer with
1-phenylsilanetriol (CA INDEX NAME)

CM 1

CRN 546114-69-6

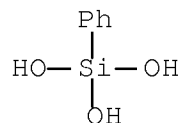
CMF C8 H12 O4 Si



CM 2

CRN 3047-74-3

CMF C6 H8 O3 Si



CC 38-3 (Plastics Fabrication and Uses)

Section cross-reference(s): 74

IT 51350-55-1P, Phenylsilanetriol homopolymer, ladder sru
157374-41-9P, Phenylsilanetriol homopolymer 475115-04-9P
1002099-61-7P 1043891-50-4P 1043891-51-5P

1071872-66-6P 1071872-67-7P 1071872-68-8P 1071872-69-9P
1071872-70-2P

RL: IMF (Industrial manufacture); PEP (Physical, engineering or chemical process); TEM (Technical or engineered material use); PREP (Preparation); PROC (Process); USES (Uses)

(silsesquioxane resin film forming composition for nanoimprinting)

RE.CNT 5 THERE ARE 5 CITED REFERENCES AVAILABLE FOR THIS RECORD
ALL CITATIONS AVAILABLE IN THE RE FORMAT

L27 ANSWER 2 OF 6 HCAPLUS COPYRIGHT 2009 ACS on STN

AN 2008:941189 HCAPLUS Full-text

DN 149:235625

TI Photosensitive composition and method for forming planarization insulating film for liquid crystal display element

IN Takeuchi, Yoshiyuki

PA Tokyo Ohka Kogyo Co., Ltd., Japan

SO PCT Int. Appl., 52pp.

CODEN: PIXXD2

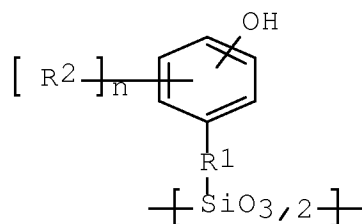
DT Patent

LA Japanese

FAN.CNT 1

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
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PI WO 2008093629	A1	20080807	WO 2008-JP51179	20080128
W: AE, AG, AL, AM, AO, AT, AU, AZ, BA, BB, BG, BH, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DO, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IS, KE, KG, KM, KN, KP, KR, KZ, LA, LC, LK, LR, LS, LT, LU, LY, MA, MD, ME, MG, MK, MN, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RS, RU, SC, SD, SE, SG, SK, SL, SM, SV, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, ZA, ZM, ZW				
RW: AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HR, HU, IE, IS, IT, LT, LU, LV, MC, MT, NL, NO, PL, PT, RO, SE, SI, SK, TR, BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG, BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW, AM, AZ, BY, KG, KZ, MD, RU, TJ, TM				
JP 2008191270	A	20080821	JP 2007-23510	20070201
PRAI JP 2007-23510	A	20070201		
GI				



I

AB The composition for forming a planarization insulating film for liquid crystal display (LCD) element contains a resin containing a constituent unit I (R1 = single bond, straight or branched chain alkylene group; R2 = alkyl; n = 0-4) and a constituent unit RSiO_{3/2} (R = aryl or alkyl), and a sensitizer. The composition enables to form a planarization insulating film having excellent transparency and heat resistance.

IT 475115-04-9 1002099-61-7

RL: TEM (Technical or engineered material use); USES (Uses)
(assumed monomers; method and compns. for forming heat-resistant transparent planarization insulating films for liquid crystal display elements)

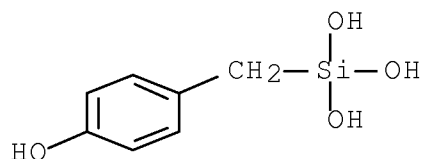
RN 475115-04-9 HCAPLUS

CN Silanetriol, 1-[(4-hydroxyphenyl)methyl]-, polymer with 1-phenylsilanetriol (CA INDEX NAME)

CM 1

CRN 188557-76-8

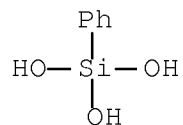
CMF C7 H10 O4 Si



CM 2

10/593,004

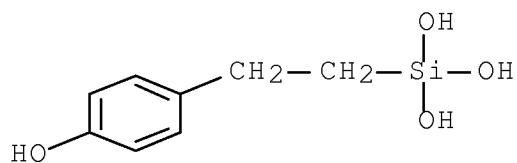
CRN 3047-74-3
CMF C6 H8 O3 Si



RN 1002099-61-7 HCAPLUS
CN Silanetriol, 1-[2-(4-hydroxyphenyl)ethyl]-, polymer with
1-phenylsilanetriol (CA INDEX NAME)

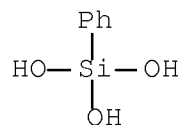
CM 1

CRN 546114-69-6
CMF C8 H12 O4 Si



CM 2

CRN 3047-74-3
CMF C6 H8 O3 Si



CC 74-13 (Radiation Chemistry, Photochemistry, and Photographic and

Other Reprographic Processes)

Section cross-reference(s): 76

IT 475115-04-9 1002099-61-7 1043891-50-4

RL: TEM (Technical or engineered material use); USES (Uses)
(assumed monomers; method and compns. for forming heat-resistant transparent planarization insulating films for liquid crystal display elements)

RE.CNT 7 THERE ARE 7 CITED REFERENCES AVAILABLE FOR THIS RECORD
ALL CITATIONS AVAILABLE IN THE RE FORMAT

L27 ANSWER 3 OF 6 HCAPLUS COPYRIGHT 2009 ACS on STN

AN 2008:90854 HCAPLUS Full-text

DN 148:179495

TI High-refractive-index materials

IN Takeuchi, Yoshiyuki

PA Tokyo Ohka Kogyo Co., Ltd., Japan

SO PCT Int. Appl., 21pp.

CODEN: PIXXD2

DT Patent

LA Japanese

FAN.CNT 1

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
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PI WO 2008010415	A1	20080124	WO 2007-JP63364	20070704
W: AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BH, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DO, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IS, KE, KG, KM, KN, KP, KR, KZ, LA, LC, LK, LR, LS, LT, LU, LY, MA, MD, ME, MG, MK, MN, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RS, RU, SC, SD, SE, SG, SK, SL, SM, SV, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, ZA, ZM, ZW				
RW: AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IS, IT, LT, LU, LV, MC, MT, NL, PL, PT, RO, SE, SI, SK, TR, BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG, BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW, AM, AZ, BY, KG, KZ, MD, RU, TJ, TM				
JP 2008024832	A	20080207	JP 2006-199237	20060721

PRAI JP 2006-199237 A 20060721

AB The high-refractive-index materials contain a siloxane resin having a structural unit $R_1R_2mSiO(3-m)/2$ (R_1 = hydrocarbon group; R_2 = H, hydrocarbon group; m = 0, 1). The materials enable to form a

waveguide by a simpler method. Also disclosed are a high-refractive-index member made from the materials, and an image sensor.

IT 475115-04-9 1002099-61-7

RL: TEM (Technical or engineered material use); USES (Uses)
(high-refractive-index materials for optical waveguides and image sensors)

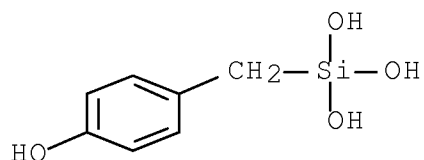
RN 475115-04-9 HCAPLUS

CN Silanetriol, 1-[(4-hydroxyphenyl)methyl]-, polymer with
1-phenylsilanetriol (CA INDEX NAME)

CM 1

CRN 188557-76-8

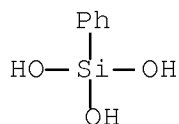
CMF C7 H10 O4 Si



CM 2

CRN 3047-74-3

CMF C6 H8 O3 Si



RN 1002099-61-7 HCAPLUS

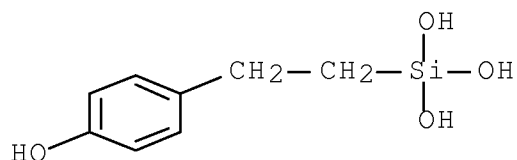
CN Silanetriol, 1-[2-(4-hydroxyphenyl)ethyl]-, polymer with
1-phenylsilanetriol (CA INDEX NAME)

CM 1

CRN 546114-69-6

10/593,004

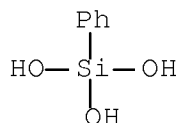
CMF C8 H12 O4 Si



CM 2

CRN 3047-74-3

CMF C6 H8 O3 Si



CC 74-13 (Radiation Chemistry, Photochemistry, and Photographic and Other Reprographic Processes)
Section cross-reference(s): 73
IT 9016-00-6, Polydimethylsilanediol, sru 31900-57-9,
Polydimethylsilanediol 51350-55-1, Phenyl silsesquioxane
157374-41-9, Phenyl silsesquioxane 475115-04-9
1002099-61-7 1002099-65-1
RL: TEM (Technical or engineered material use); USES (Uses)
(high-refractive-index materials for optical waveguides and image sensors)
RE.CNT 8 THERE ARE 8 CITED REFERENCES AVAILABLE FOR THIS RECORD
ALL CITATIONS AVAILABLE IN THE RE FORMAT

L27 ANSWER 4 OF 6 HCAPLUS COPYRIGHT 2009 ACS on STN
AN 2007:964078 HCAPLUS Full-text
DN 147:312575
TI Method for manufacturing organic semiconductor device and composition for forming insulating film used therein
IN Ogata, Toshiyuki; Kawana, Daisuke; Hada, Hideo; Takahashi, Motoki; Ohmori, Yutaka; Kajii, Hirotake

PA Tokyo Ohka Kogyo Co., Ltd., Japan; Osaka University

SO PCT Int. Appl., 43pp.

CODEN: PIXXD2

DT Patent

LA Japanese

FAN.CNT 1

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
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PI	WO 2007097212	A1	20070830	WO 2007-JP52345	20070209
	W: AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IS, KE, KG, KM, KN, KP, KR, KZ, LA, LC, LK, LR, LS, LT, LU, LV, LY, MA, MD, MG, MK, MN, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RS, RU, SC, SD, SE, SG, SK, SL, SM, SV, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, ZA, ZM, ZW				
	RW: AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IS, IT, LT, LU, LV, MC, NL, PL, PT, RO, SE, SI, SK, TR, BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG, BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW, AM, AZ, BY, KG, KZ, MD, RU, TJ, TM				
	JP 2007258663	A	20071004	JP 2006-221829	20060816
PRAI	JP 2006-45273	A	20060222		
	JP 2006-221829	A	20060816		

AB Disclosed is a composition for forming an insulating film, which is capable of reducing spaces between mols., thereby forming a dense insulating film. Also disclosed are an insulating film and an organic semiconductor device which can be driven at a low voltage while having a stable driving voltage by using such an insulating film. Specifically disclosed is a composition for forming an insulating film between a gate electrode layer and an organic semiconductor film layer in an organic semiconductor device, which composition contains a resin component (A) having a silsesquioxane backbone. The resin component (A) is composed of a resin (A1) having a structural unit represented by the general formula $-(\text{SiO}_{3/2}((\text{R}_2)_n\text{X-OR}_1)-)-$, where, X represents an alkylene group having 1-15 C atoms or a divalent aromatic hydrocarbon group having 6-15 C atoms; R1 represents a H atom, an alkyl group having 1-15 C atoms or an alkoxyalkyl group having 2-15 C atoms; R2 represents an alkyl group having 1-4 C atoms; and n represents 0 or 1.

IT 475115-04-9

RL: TEM (Technical or engineered material use); USES (Uses)

(method for manufacturing organic TFT and composition for forming insulating

film used therein)

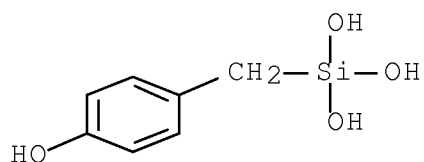
RN 475115-04-9 HCAPLUS

CN Silanetriol, 1-[(4-hydroxyphenyl)methyl]-, polymer with
1-phenylsilanetriol (CA INDEX NAME)

CM 1

CRN 188557-76-8

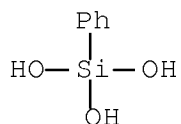
CMF C7 H10 O4 Si



CM 2

CRN 3047-74-3

CMF C6 H8 O3 Si



CC 76-3 (Electric Phenomena)

IT 2386-87-0 3089-11-0 17464-88-9 151271-43-1,

α, ω -Dihexyl-sexithiophene	160848-22-6	193345-23-2
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475115-04-9 711008-00-3 882004-77-5 947265-31-8

RL: TEM (Technical or engineered material use); USES (Uses)

(method for manufacturing organic TFT and composition for forming insulating

film used therein)

RE.CNT 30 THERE ARE 30 CITED REFERENCES AVAILABLE FOR THIS RECORD
ALL CITATIONS AVAILABLE IN THE RE FORMAT

L27 ANSWER 5 OF 6 HCAPLUS COPYRIGHT 2009 ACS on STN

AN 2005:672696 HCAPLUS Full-text

DN 143:176216

TI Solid electrolyte proton conductor membrane electrode assembly for fuel cell

IN Wariishi, Koji; Ono, Michio; Nomura, Kimiatsu

PA Fuji Photo Film Co., Ltd., Japan

SO U.S. Pat. Appl. Publ., 36 pp.

CODEN: USXXCO

DT Patent

LA English

FAN.CNT 2

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
	-----	----	-----	-----	
PI	US 20050164063	A1	20050728	US 2004-969530	20041020
	JP 2005248152	A	20050915	JP 2004-289019	20040930

PRAI JP 2003-359927 A 20031020

JP 2004-25055 A 20040202

AB A solid electrolyte having a high ionic conductivity and not so much troubled by methanol-crossover through it is provided according to a method of sulfonation of a compound of the formula $[(R1O)mSi(R2)3-mL1)nAr1]pL2$ wherein R1 represents H, an alkyl group, an aryl group or a silyl group; R2 represents an alkyl group, an aryl group or a heterocyclic group; m indicates an integer of from 1 to 3; L1 represents a single bond, an alkylene group, -O-, -CO-, or a divalent linking group of a combination of any of these groups; L2 represents an n-valent linking group; Ar1 represents an arylene or heteroarylene group having at least one electron-donating group; p indicates an integer of from 2 to 4; n indicates an integer of 1 or 2 followed by sol-gel reaction of the resulting compound, or according to a method of the sol-gel reaction followed by the sulfonation.

IT 861098-58-0DP, sulfonated

RL: DEV (Device component use); SPN (Synthetic preparation); PREP (Preparation); USES (Uses)

(solid electrolyte proton conductor membrane electrode assembly for fuel cell)

RN 861098-58-0 HCAPLUS

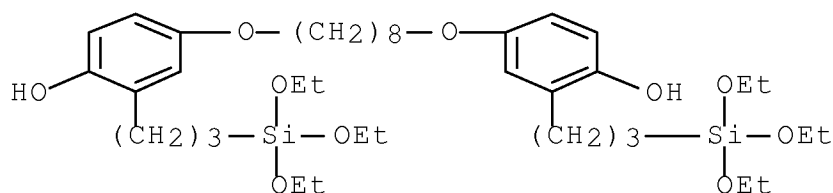
CN Phenol, 4,4'-[1,8-octanediylbis(oxy)]bis[2-[3-(triethoxysilyl)propyl]-, polymer with triethoxyphenylsilane (9CI) (CA INDEX NAME)

10/593,004

CM 1

CRN 861098-54-6

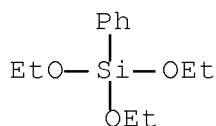
CMF C38 H66 O10 Si2



CM 2

CRN 780-69-8

CMF C12 H20 O3 Si



IC ICM H01M008-10

ICS C07F007-04

INCL 429033000; 556482000

CC 52-2 (Electrochemical, Radiational, and Thermal Energy Technology)
Section cross-reference(s): 47

IT	51350-55-1DP, sulfonated	124741-08-8DP, sulfonated
	141087-51-6DP, sulfonated	152791-93-0DP, sulfonated
	852921-77-8DP, sulfonated	852921-78-9DP, sulfonated
	861098-36-4DP, sulfonated	861098-37-5DP, sulfonated
	861098-38-6DP, sulfonated	861098-39-7DP, sulfonated
	861098-40-0DP, sulfonated	861098-41-1DP, sulfonated
	861098-43-3DP, sulfonated	861098-44-4DP, sulfonated
	861098-46-6DP, sulfonated	861098-47-7DP, sulfonated
	861098-48-8DP, sulfonated	861098-49-9DP, sulfonated
	861098-50-2DP, sulfonated	861098-53-5DP, sulfonated
	861098-55-7DP, sulfonated	861098-57-9DP, sulfonated

861098-58-0DP, sulfonated 861098-60-4DP, sulfonated
 861098-62-6DP, sulfonated 861098-63-7DP, sulfonated
 861098-64-8DP, sulfonated 861098-65-9DP, sulfonated
 861098-66-0DP, sulfonated 861098-67-1DP, sulfonated

RL: DEV (Device component use); SPN (Synthetic preparation); PREP
 (Preparation); USES (Uses)

(solid electrolyte proton conductor membrane electrode assembly
 for fuel cell)

L27 ANSWER 6 OF 6 HCAPLUS COPYRIGHT 2009 ACS on STN

AN 1996:745487 HCAPLUS Full-text

DN 126:13061

OREF 126:2645a,2648a

TI Electrophotographic photoreceptor with uppermost layer containing
 polyester with siloxane structure

IN Itami, Akihiko; Asano, Masanari

PA Konishiroku Photo Ind, Japan

SO Jpn. Kokai Tokkyo Koho, 43 pp.

CODEN: JKXXAF

DT Patent

LA Japanese

FAN.CNT 1

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
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PI	JP 08234468	A	19960913	JP 1995-37062	199502 24

PRAI JP 1995-37062 19950224

AB The uppermost layer contains a copolymer with polyester-polycarbonate
 and polysiloxane structures or polyester with polysiloxane structure.
 The photoreceptor shows with sensitivity, abrasion resistance, and
 printing durability.

IT 184155-93-9

RL: DEV (Device component use); USES (Uses)

(electrophotog. photoreceptor with uppermost layer containing
 polyester with siloxane structure)

RN 184155-93-9 HCAPLUS

CN Benzoic acid, 4,4'-methylenebis-, polymer with

α -[[4-(4-hydroxyphenyl)butyl]methylphenylsilyl]- ω -[[[4-
 (4-hydroxyphenyl)butyl]methylphenylsilyl]oxy]poly[oxy(methylphenylsi
 lylene)] (9CI) (CA INDEX NAME)

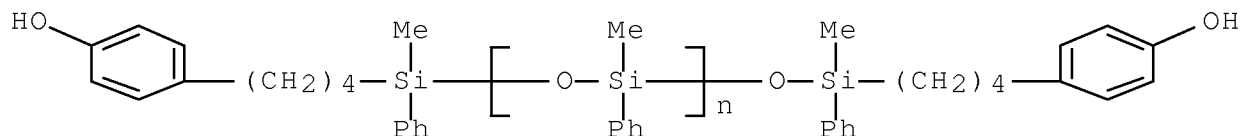
CM 1

CRN 184155-92-8

CMF (C7 H8 O Si)_n C₃₄ H₄₂ O₃ Si₂

10/593,004

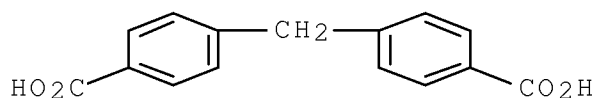
CCI PMS



CM 2

CRN 790-83-0

CMF C15 H12 O4



IC ICM G03G005-147

ICS G03G005-05

CC 74-3 (Radiation Chemistry, Photochemistry, and Photographic and Other Reprographic Processes)

Section cross-reference(s): 38

IT	184155-65-5	184155-66-6	184155-67-7	184155-68-8	184155-70-2
	184155-71-3	184155-75-7	184155-77-9	184155-79-1	184155-80-4
	184155-82-6	184155-84-8	184155-86-0	184155-88-2	184155-90-6
	184155-91-7	184155-93-9	184155-95-1	184155-96-2	
	184155-97-3	184155-98-4	184156-00-1	184156-03-4	184156-04-5
	184156-05-6	184156-06-7	184156-07-8	184156-09-0	184156-12-5
	184156-15-8	184156-17-0	184156-19-2	184156-21-6	184156-23-8
	184156-46-5				

RL: DEV (Device component use); USES (Uses)

(electrophotog. photoreceptor with uppermost layer containing polyester with siloxane structure)

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